MSKSEMI















ESD

TVS

TSS

MOV

GDT

PLED

Broduct data sheet





SOT-89

Daalyaga	Pin	assignn	signment		
Package	1	2	3		
SOT-89	T1	Т2	G		

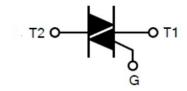
FEATURES

- Direct interfacing to logic level ICs
- Direct interfacing to low power gate drivers and microcontrollers
- High blocking voltage capability
- Planar passivated for voltage ruggedness and reliability
- Triggering in all four quadrants
- Very sensitive gate

APPLICATIONS

- General purpose bidirectional switching
- General purpose low power phase control
- General purpose low power switching
- Solid-state relay

SYMBOL:



ABSOLUTE MAXIMUM RATINGS

PARAMETER	SYMBOL	VALUE		UNIT		
Panatitiva Paak Off State Voltages	V _{DRM,} V _{RRM}	MAC97A6 400		V		
Repetitive Peak Off-State Voltages		MAC9	MAC97A8 600] V	
RMS on-State Current	I _{T(RMS)}		8.0		Α	
Non-Repetitive Peak On-State Current	I _{TSM}		8		Α	
I ² t for fusing	l²t		0.32		A ² s	
	JIT/-14	I		50		
Repetitive rate of rise of on-state current after triggering		II		50	A /C	
	dIT/dt	III		50	A/uS	
		IV		10		
Peak gate current	I _{GM}		1		Α	
Peak Gate Voltage	V_{GM}		5		V	
Peak Gate Power	P_{GM}		5		W	
Average Gate Power	$P_{G(AV)}$		0.1		W	
Operating junction temperature	TJ		+125		$^{\circ}$	
Storage Temperature	T _{STG}	_	40 ~ +1	150	$^{\circ}$	

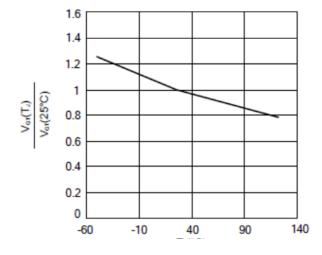


ELECTRICAL CHARACTERISTICS (TJ=25°C)

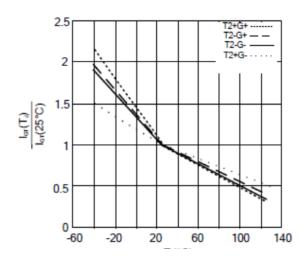
PARAMETER	SYMBOL	TEST CONDITIONS		MIN	MAX	UNITS
Peak Repetitive Forward or Reverse Blocking Current	I _{DRM} I _{RRM}	V_{AK} = Rated V_{DRM} or V_{RRM} ;			10	uA
			I		5.0	
Gate Trigger Current	I _{GT}	$V_D = 12V$ $I_{GT} = 0.1A$	II		5.0	mA
			III		5.0	
			IV		7.0	
Gate Trigger Voltage	V_{GT}	$V_D=12V$, RL= 100Ω			2.0	V
Peak Forward On-State Voltage	V _{TM}	IT=1.0A,			1.7	V
			I		10	
Holding Current	IL	V _D =12V	II		20	m ^
		I _G =0.1A,	III		10	mA
			IV		10	
Latch Current	I_{H}	V _D =12V ,IG=0.1A			10	mA
Critical Rate of Rise of Off-State Voltage	dV/dt	$V_D=67\%V_{DRM}, R_{GK}=1k\Omega,$		10		V/µs

ELECTRICAL CHARACTERISTIC CURVE

Normalized Gate Trigger Voltage as a of Function Junction Temperature; Typical Values.



Normalized Gate Trigger Current as a Function of Junction Temperature; Typical Values.

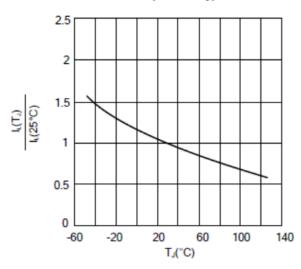




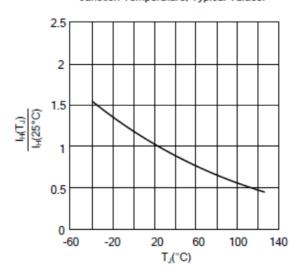




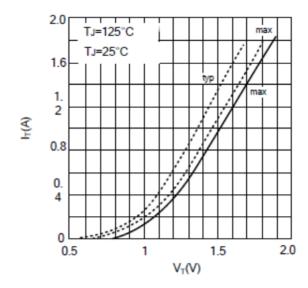
Normalized Latching Current as a Function of Junction Temperature; Typical Values.



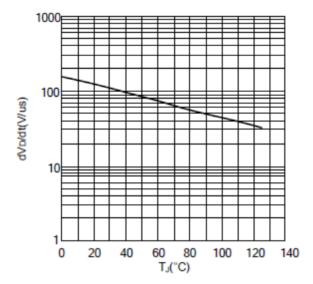
Normalized Holding Current as a Function of Junction Temperature; Typical Values.



On-State Current as a Function of On-State Voltage; Typical and Maximum Values.

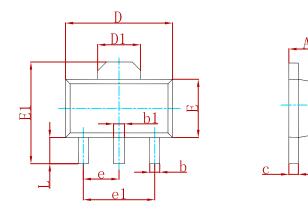


Critical Rate of Rise of Off-State Voltage as a Function of Junction Temperature; Typical Values.



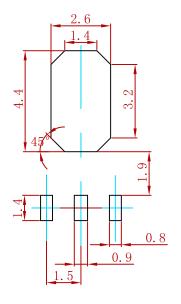


PACKAGE MECHANICAL DATA



Symbol	Dimensions In Millimeters		Dimension	s In Inches
Symbol	Min	Max	Min	Max
Α	1.400	1.600	0.055	0.063
b	0.320	0.520	0.013	0.020
b1	0.400	0.580	0.016	0.023
С	0.350	0.440	0.014	0.017
D	4.400	4.600	0.173	0.181
D1	1.550 REF.		0.061 REF.	
E	2.300	2.600	0.091	0.102
E1	3.940	4.250	0.155	0.167
е	1.500 TYP.		0.060 TYP.	
e1	3.000 TYP.		0.118 TYP.	
L	0.900	1.200	0.035	0.047

Suggested Pad Layout



Note:

- 1.Controlling dimension:in millimeters.
- 2.General tolerance:±0.05mm.
- 3. The pad layout is for reference purposes only.

REEL SPECIFICATION

P/N	PKG	QTY
MAC97A6 THRU MAC97A8	SOT-89	1000



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